

-- Preferred embodiments of this invention are to be described in detail with reference to the drawings. Figs. 1A and 1B are an example of schematic step charts illustrating a method of manufacturing a thin film semiconductor device according to this invention. At first, as shown in Fig. 1A, a manufacturing substrate 20 having characteristics durable to the process for forming a thin film transistor and a product substrate 1 having characteristics suitable to direct mounting of a thin film transistor are prepared. In the preparatory step, a manufacturing substrate 20, for example, made of an inorganic material, such as glass, and a product substrate 1 made of an organic material, such as plastic, are prepared. In this embodiment, non-alkali glass is used as the manufacturing substrate 20. The heat resistance of the non-alkali glass is about 500(C. The standard thickness for the manufacturing substrate 20 is, for example, 0.7 mm. If it is reduced to 0.5 mm, there is no particular problem in view of the manufacturing process. In this embodiment, non-alkali glass is used but, instead, metal plate, such as of stainless steel, plastic plate, quartz and the like, can be also be used. On the other hand, for the product substrate 1, it is necessary to have a heat resistance capable of withstanding the processing temperature of a thin film transistor, and it is necessary that the substrate is thinner and lighter compared with the manufacturing substrate 20. In this embodiment, a plastic material is used with a thickness from about 0.1 mm to 0.5 mm.

Particularly, polyether sulfone resin (PES), polyethylene terephthalate resin or ARTON resin of excellent heat resistance is used. The polyether sulfone resin has a heat resistance as high as about 250(C. The plastic film used for the product substrate 1 may be a single layer and, depending on the case, has a laminate structure. Particularly, when this is used for a reflection type display and not a transmission type display, a metal plate can be used instead of the plastic material.

However, when the metal plate is used, the surface has to be insulated. For example, when an aluminum plate is used for the product substrate 1, the surface has to be previously covered with alumina. --

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Please replace the paragraph beginning at page 9, line 25 with the following rewritten paragraph.

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-- In the embodiment described above, a thin film transistor of the bottom gate structure has been formed on the substrate 1. Instead, a thin film transistor of a top gate structure may also be integrated and formed. Fig. 3 shows this embodiment. For easy understanding, corresponding reference numerals are attached to those portions corresponding to the previous embodiment shown in Fig. 1 and Fig. 2. As shown in the drawing, in the thin film transistor of the top gate structure, the gate electrode 5 is formed by way of the gate insulation film 4 on the semiconductor